

Features

- Uses CRM(CQ) advanced SkyMOS4 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Applications

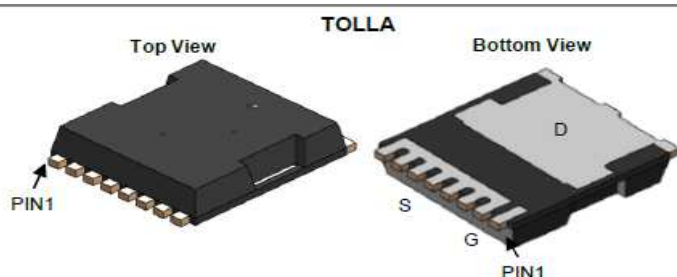
- Motor control and drive
- Battery management
- UPS (Uninterruptible Power Supplies)

Product Summary

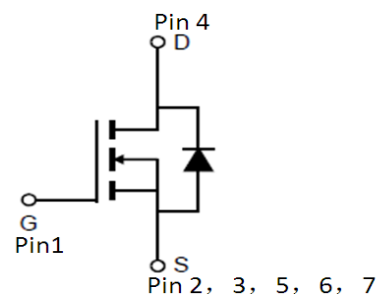
V_{DS}	100V
$R_{DS(on)}$	1.75mΩ
I_D	248A

100% DVDS Tested

100% Avalanche Tested



CRSZ019N10N4Z



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRSZ019N10N4Z	-	TOLLA	Tube	N/A	N/A	50pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	100	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$ (Silicon limit)	I_D	262 248 166	A
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D \text{ pulse}}$	992	A
Avalanche energy, single pulse ($L=0.5\text{mH}$, $R_g=25\Omega$) ^[1]	E_{AS}	500	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	250	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ\text{C}$

Notes:1.EAS was tested at $T_j = 25^\circ\text{C}$, $I_D = 45\text{A}$.

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.50	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	55	

Electrical Characteristic (at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	100	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	2.2	3	3.8	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	0.05	1	μA	$V_{DS}=100V, V_{GS}=0V$ $T_j=25^{\circ}\text{C}$ $T_j=125^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	± 10	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.75	2.1	mΩ	$V_{GS}=10V, I_D=100A$
Transconductance	g_{fs}	-	275	-	S	$V_{DS}=5V, I_D=100A$

Dynamic Characteristic

Input Capacitance	C_{iss}	7565	11347	17020.5	pF	$V_{GS}=0V, V_{DS}=50V,$ $f=1\text{MHz}$
Output Capacitance	C_{oss}	1167	1751	4376		
Reverse Transfer Capacitance	C_{rss}	25	37	259		
Gate Total Charge	Q_G	100	157	200	nC	$V_{GS}=10V, V_{DS}=50V,$ $I_D=100A, f=1\text{MHz}$
Gate-Source charge	Q_{gs}	30	66	100		
Gate-Drain charge	Q_{gd}	12	18	35		

Turn-on delay time	$t_{d(on)}$	19	29	43	ns	$V_{GS}=10V, V_{DD}=50V,$ $R_{G_ext}=3.0\Omega$
Rise time	t_r	76	114	170		
Turn-off delay time	$t_{d(off)}$	52	78	117		
Fall time	t_f	72	109	163		
Gate resistance	R_G	1	1.6	2.5	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.9	1.4	V	$V_{GS}=0V, I_{SD}=100A$
Body Diode Continuous Forward Current	I_S	-	-	248	A	$T_C = 25^\circ C$
Body Diode Pulsed Current	$I_{S\ pulse}$	-	-	992	A	$T_C = 25^\circ C$
Body Diode Reverse Recovery Time	t_{rr}	49	99	197	ns	$I_F=100A,$ $dI/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	109	218	436	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

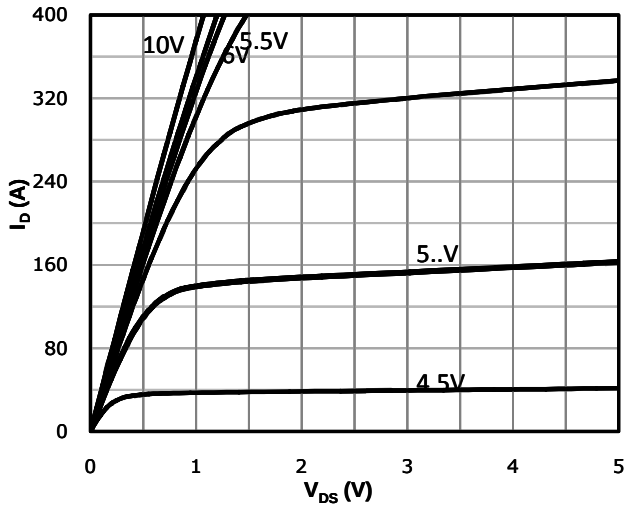
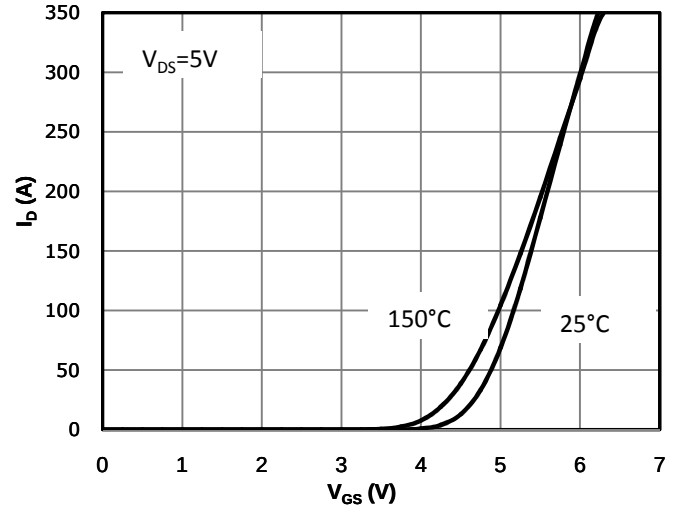


Fig 2: Transfer Characteristics



3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

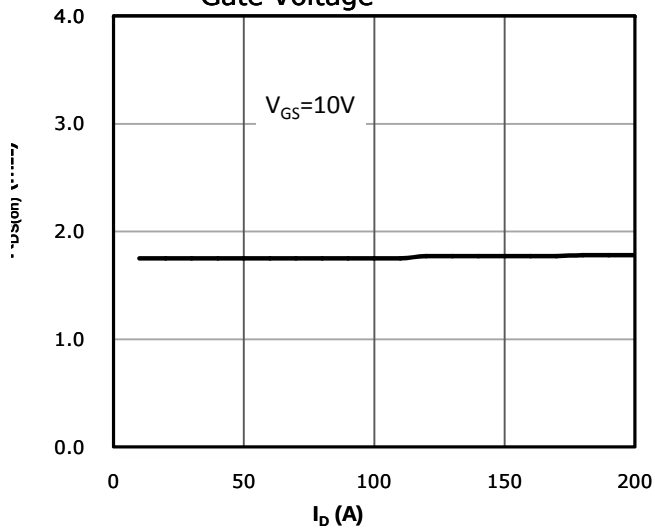


Fig 4: $R_{DS(on)}$ vs Gate Voltage

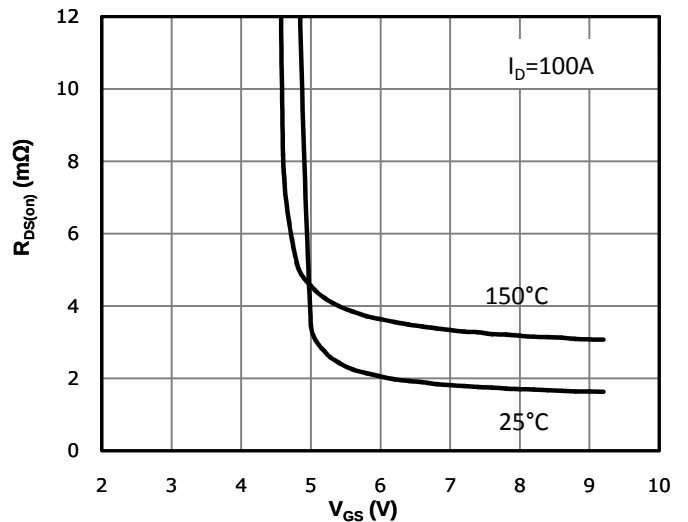


Fig 5: $R_{DS(on)}$ vs. Temperature

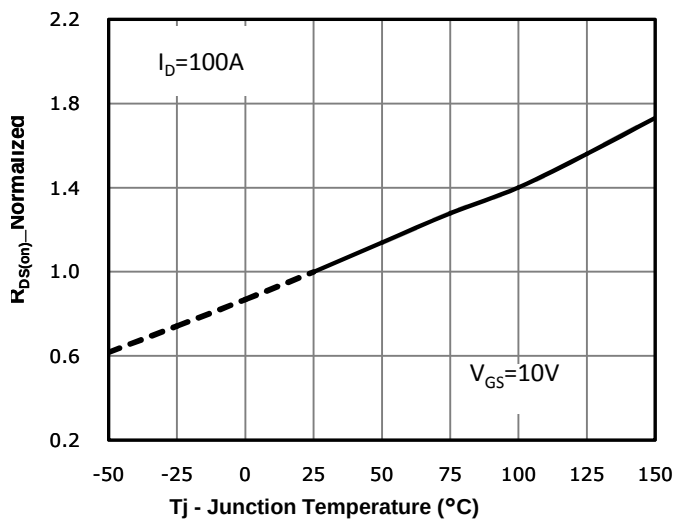


Fig 6: $V_{GS(th)}$ vs. Temperature

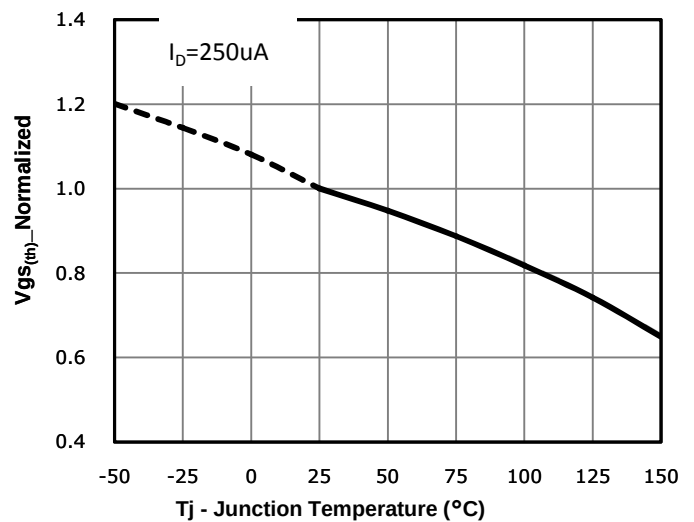


Fig 7: BVds vs. Temperature

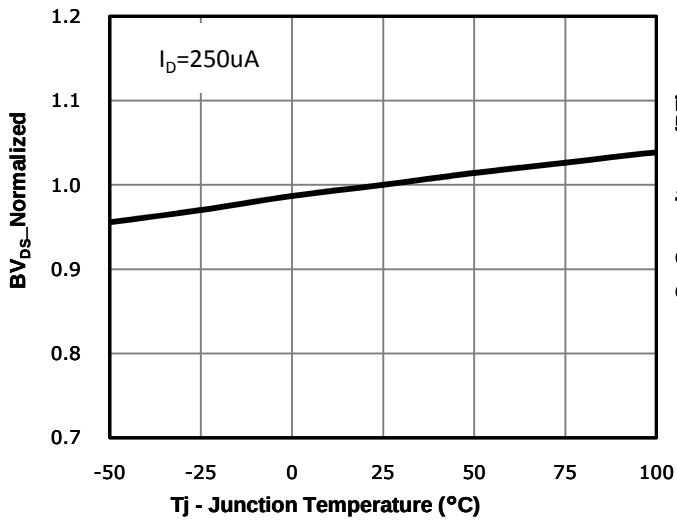


Fig 8: Capacitance Characteristics

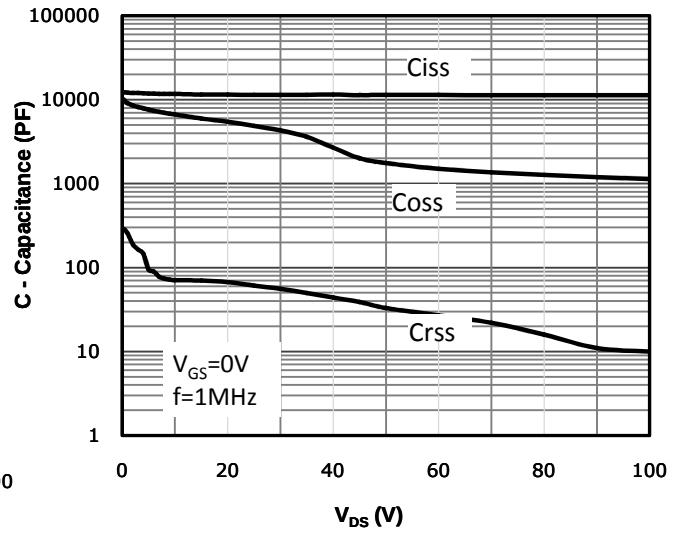


Fig 9: Gate Charge Characteristics

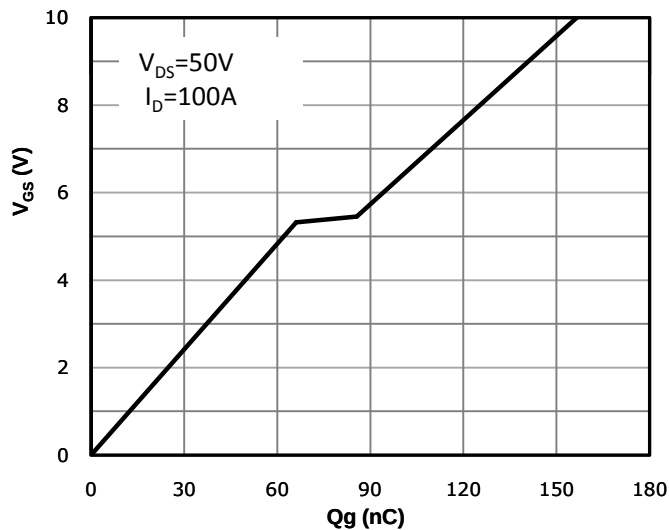


Fig 10: Body-diode Forward Characteristics

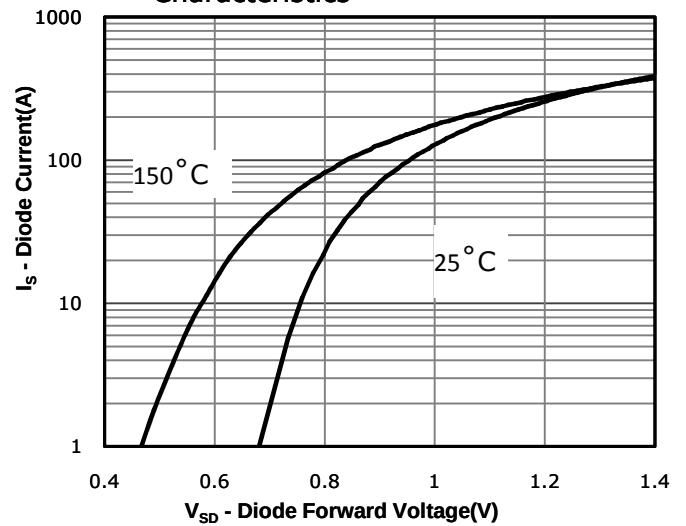


Fig 11: Power Dissipation

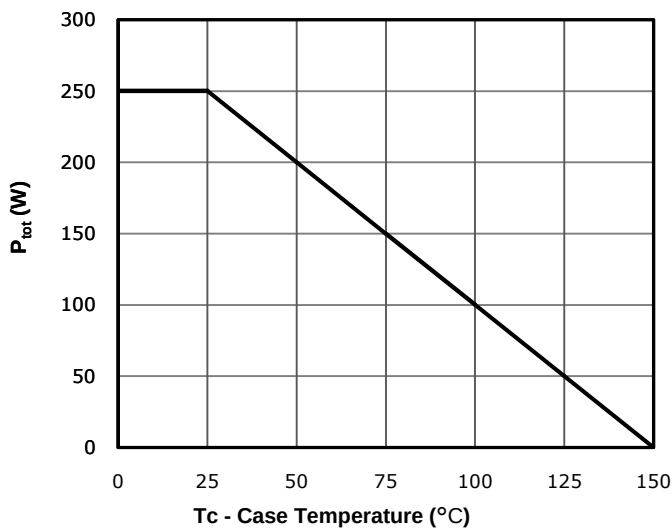


Fig 12: Drain Current Derating

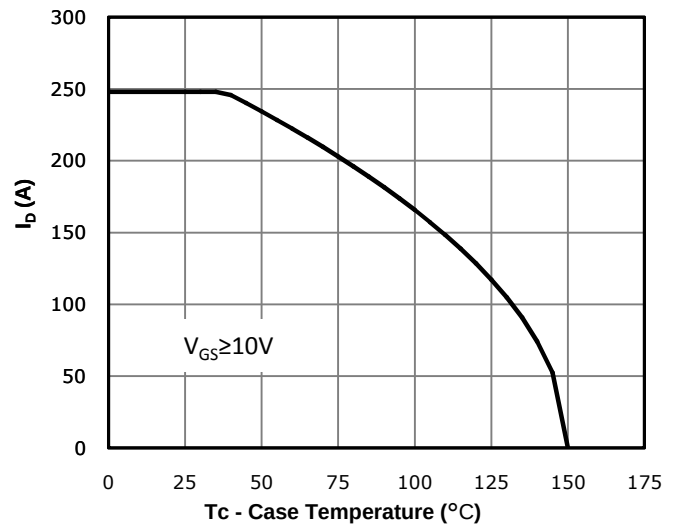


Fig 13: Safe Operating Area

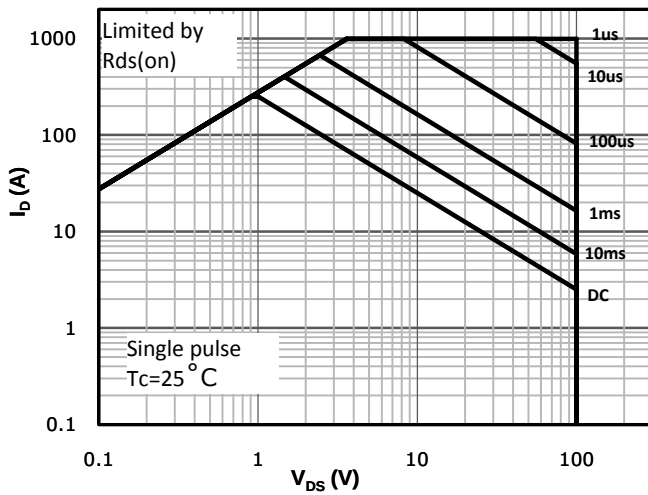
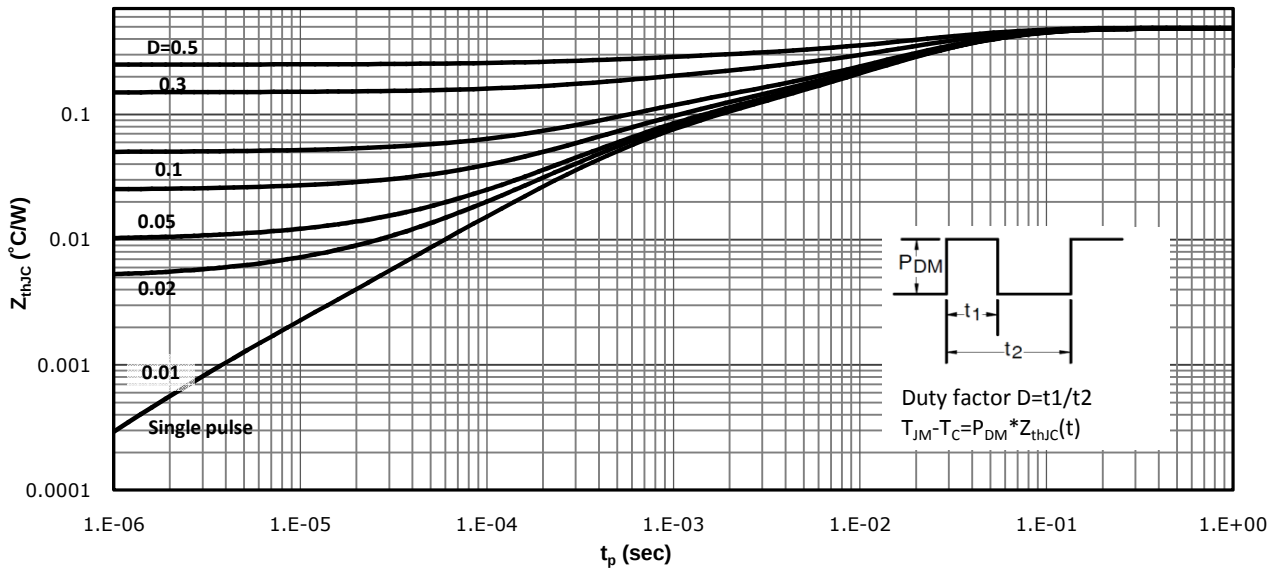
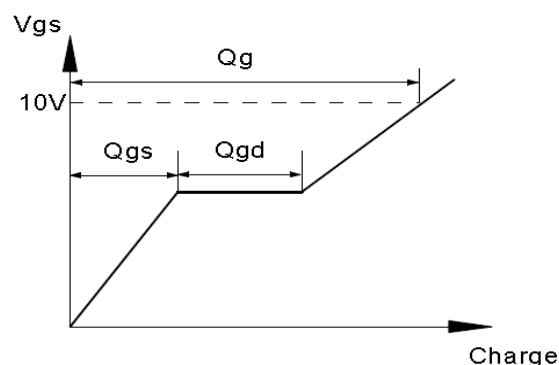
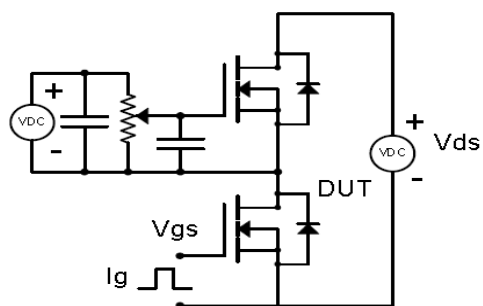


Fig 13: Max. Transient Thermal Impedance

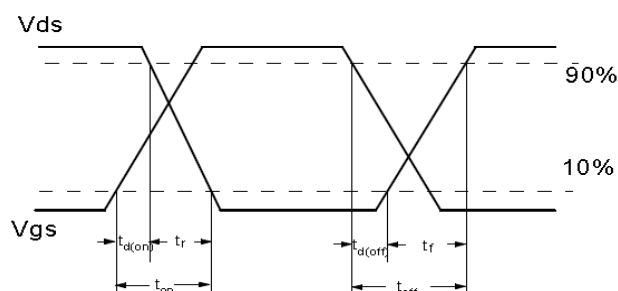
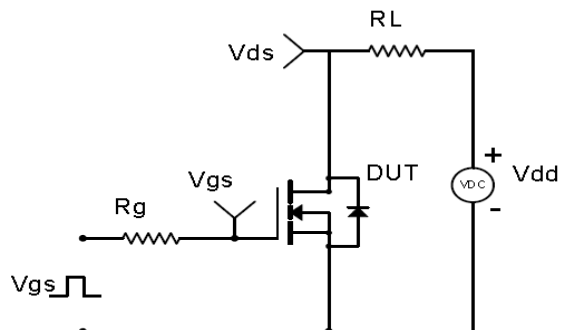


Test Circuit & Waveform

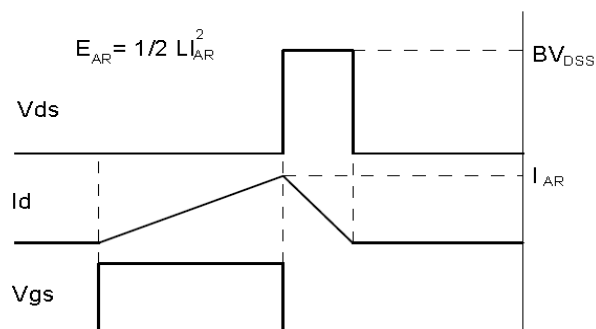
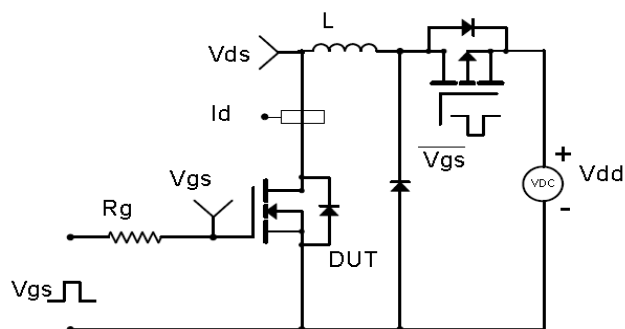
Gate Charge Test Circuit & Waveform



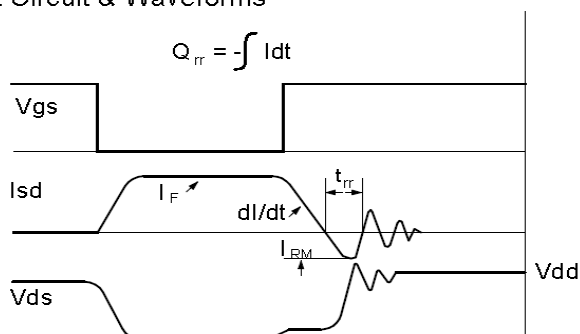
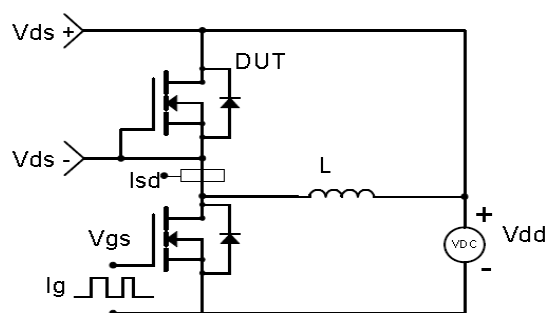
Resistive Switching Test Circuit & Waveforms



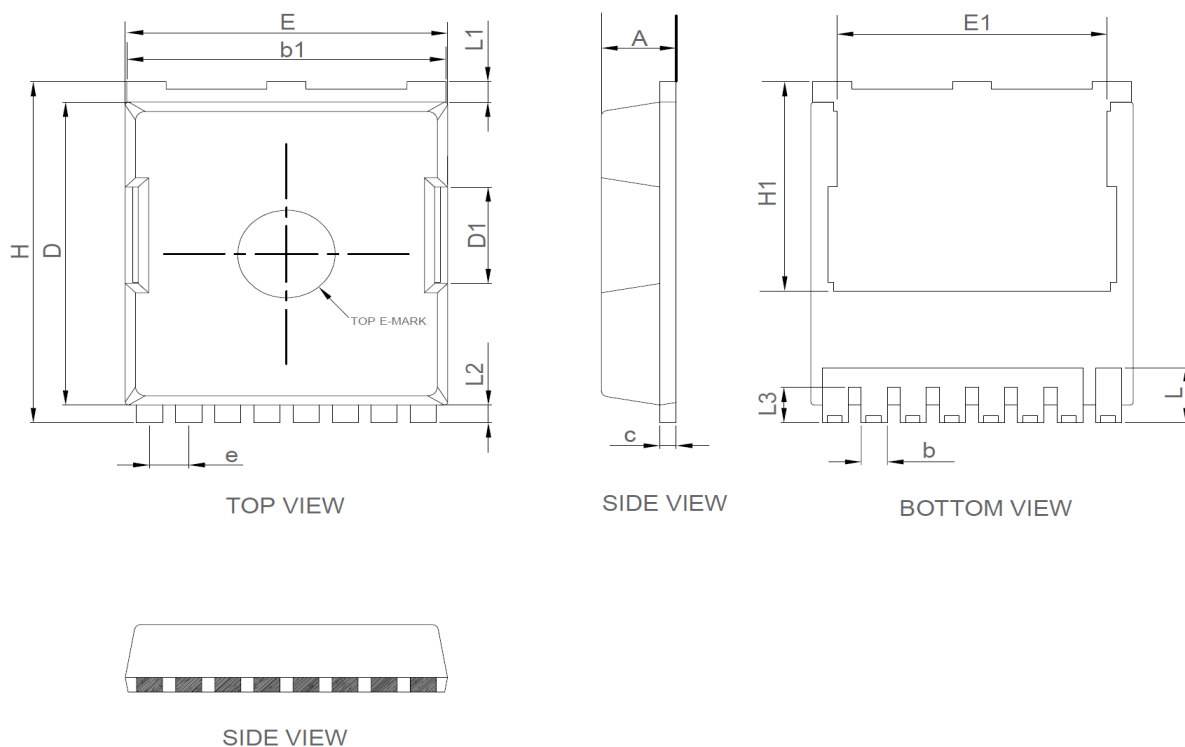
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TOLL



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.15	2.45	0.085	0.096
b	0.60	0.90	0.024	0.035
b1	9.65	9.95	0.380	0.392
c	0.35	0.65	0.014	0.026
D	10.18	10.70	0.401	0.421
D1	3.15	3.45	0.124	0.136
E	9.70	10.10	0.382	0.398
E1	7.35	8.45	0.289	0.333
e	1.10	1.30	0.043	0.051
H	11.45	11.95	0.451	0.470
H1	6.55	7.50	0.258	0.295
L	1.35	2.10	0.053	0.083
L1	0.50	0.90	0.020	0.035
L2	0.40	0.80	0.016	0.031
L3	0.95	1.35	0.037	0.053

Revision History

Revision	Date	Major changes
1.0	30/8/2022	Release of Preliminary version

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.